

RENESAS

HSM226S

Silicon Schottky Barrier Diode for High speed switching

REJ03G0057-0100Z

Rev.1.00

Jan.21.2004

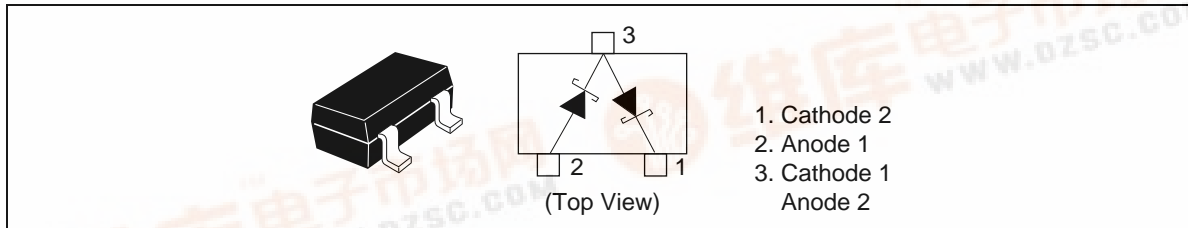
Features

- Low reverse current, Low capacitance.
- MPAK Package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HSM226S	S22	MPAK

Pin Arrangement



HSM226S

Absolute Maximum Ratings

(T_a = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V _{RRM}	25	V
Non-Repetitive peak forward surge current	I _{FSM} *1 *2	200	mA
forward current	I _F *2	50	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

Notes: 1. 10 ms sine wave 1 pulse
2. Two device total

Electrical Characteristics

(T_a = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V _{F1}	—	—	0.33	V	I _F = 1 mA
	V _{F2}	—	—	0.38		I _F = 5 mA
Reverse current	I _R	—	—	0.45	μA	V _R = 20 V
Capacitance	C	—	—	2.80	pF	V _R = 1 V, f = 1 MHz

Note: Per one device

Main Characteristic

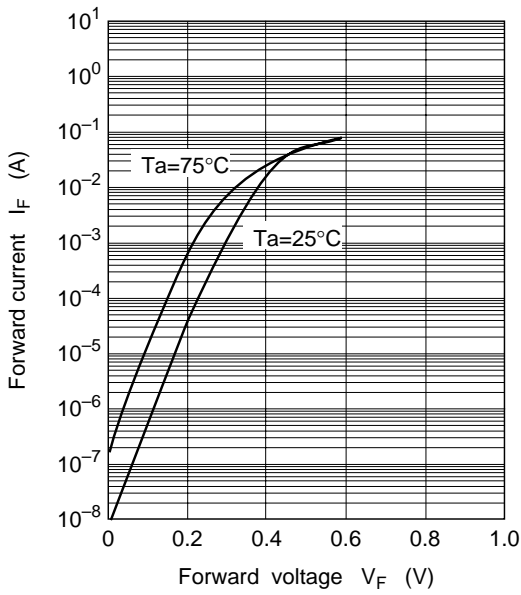


Fig.1 Forward current vs. Forward voltage

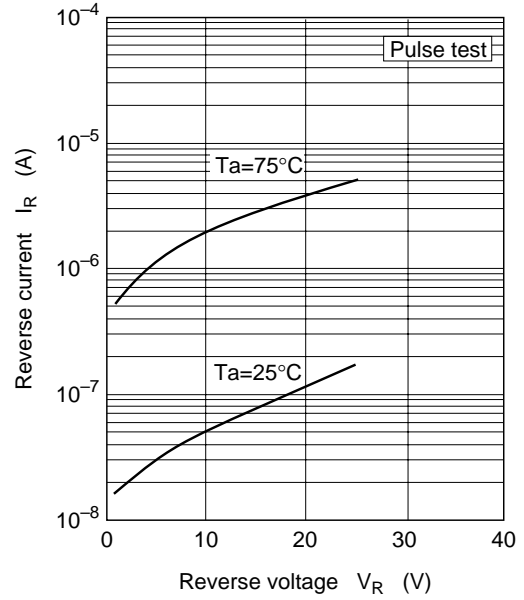


Fig.2 Reverse current vs. Reverse voltage

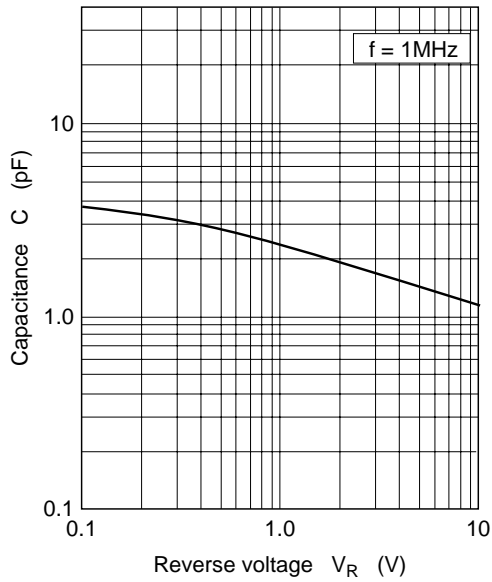
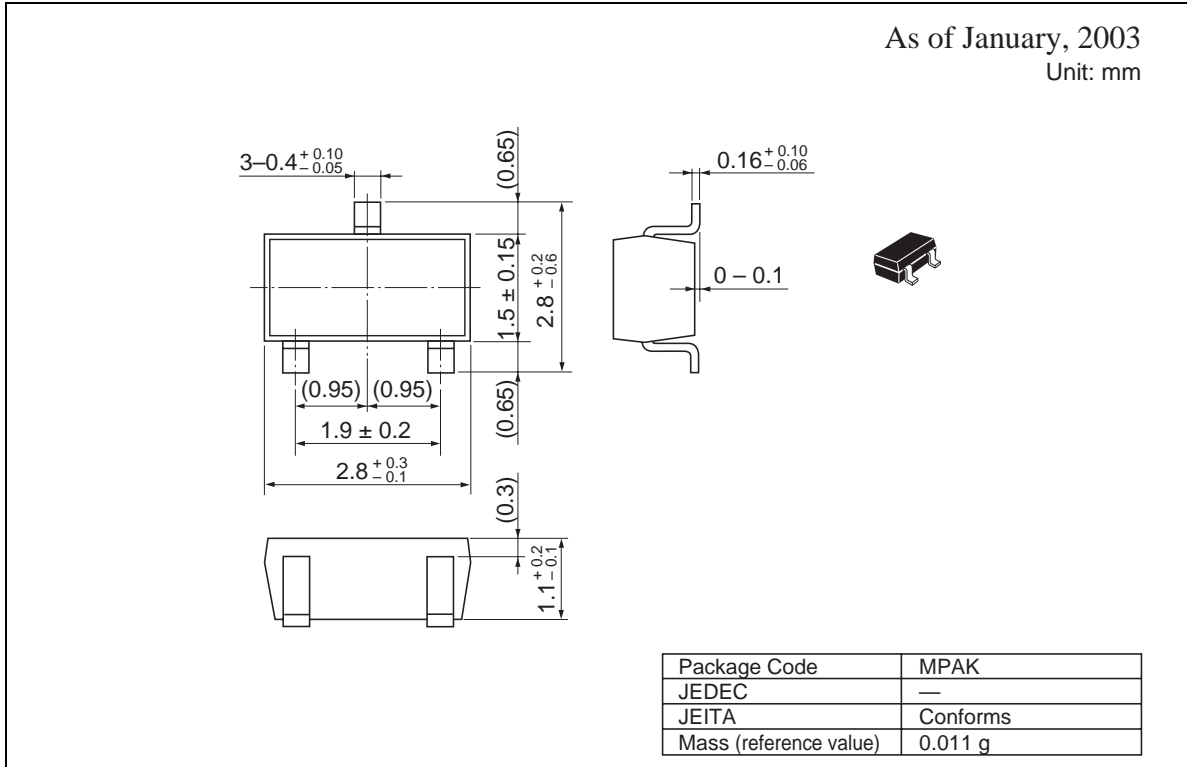


Fig.3 Capacitance vs. Reverse voltage

HSM226S

Package Dimensions



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